

CY7C1049GN

4-Mbit (512K words × 8-bit) Static RAM

Features

- High speed □ t_{AA} = 10 ns
- Low active and standby currents
 Active current: I_{CC} = 38 mA typical
 Standby current: I_{SB2} = 6 mA typical
- Operating voltage range: 1.65 V to 2.2 V, 2.2 V to 3.6 V, and 4.5 V to 5.5 V
- 1.0 V data retention
- TTL-compatible inputs and outputs
- Pb-free 36-pin SOJ and 44-pin TSOP II packages

Functional Description

CY7C1049GN is a high-performance CMOS fast static RAM device organized as 512K words by 8-bits.

Data writes are performed by asserting the Chip Enable (\overline{CE}) and Write Enable (\overline{WE}) inputs LOW, while providing the data on I/O₀ through I/O₇ and address on A₀ through A₁₈ pins.

Data reads are performed by asserting the Chip Enable (\overline{CE}) and Output Enable (\overline{OE}) inputs LOW and providing the required address on the address lines. Read data is accessible on the I/O lines (I/O₀ through I/O₇).

All I/Os (I/O $_0$ through I/O $_7$) are placed in a high-impedance state during the following events:

- The device is deselected (CE HIGH)
- The control signal OE is de-asserted

The logic block diagram is on page 2.

		V Banga (II)	Speed (ns)	Power Dissipation				
Product	Bongo			Operating I _{CC} , (mA)		Standby, I _{SB2} (mA)		
Floudet	Range	V _{CC} Range (V)	10/15	f = 1	f = f _{max} Star		muby, I _{SB2} (mA)	
			10,10	Typ ^[1]	Max	Typ ^[1]	Max	
CY7C1049GN18	Industrial	1.65 V–2.2 V	15	_	40	6	8	
CY7C1049GN30		2.2 V–3.6 V	10	38	45			
CY7C1049GN		4.5 V–5.5 V	10	38	45			

Product Portfolio

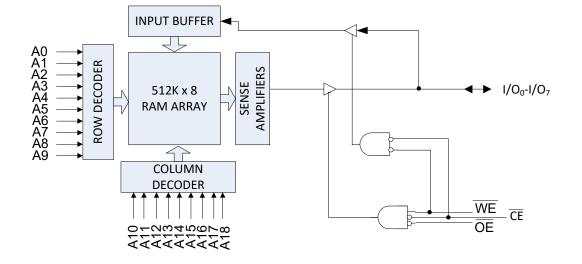
Note

1. Typical values are included only for reference and are not guaranteed or tested. Typical values are measured at V_{CC} = 1.8 V (for a V_{CC} range of 1.65 V–2.2 V), V_{CC} = 3 V (for a V_{CC} range of 2.2 V–3.6 V), and V_{CC} = 5 V (for a V_{CC} range of 4.5 V–5.5 V), T_A = 25 °C.

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Logic Block Diagram – CY7C1049GN





CY7C1049GN

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Pin Configurations

Figure 1. 36-pin SOJ pinout ^[2]

1			
A0 🗖	•1	\bigcirc	36 = NC
A1 🗖	2		35 🗖 A18
A2 🗖	3		34 🗖 A17
Аз 🗖	4		33 🗖 A16
A4 🗖	5		32 🗖 A15
CE 🗖	6		31 🗖 🖸
I/Oo 🗖	7		30 🗖 I/O7
I/O1 🗖	8		29 🗖 I/O6
Vcc 🗖	9		28 🗖 GND
GND 🗖	10	SOJ	27 🗖 Vcc
I/O2 🗖	11		26 🗖 I/O5
I/O3 🗖	12		25 🗖 I/O4
WE 🗖	13		24 🗖 A14
A5 🗖	14		23 🗖 A13
A6 🗖	15		22 🗖 A12
A7 🗖	16		21 🗖 A11
A8 🗖	17		20 🗖 A10
A9 🗖	18		19 = NC

Figure 2. 44-pin TSOP II pinout, Single Chip Enable ^[2]

1	•			1
NC 🗖	1		44	NC NC
NC 🗖	2		43	NC NC
A0 🗖	3		42	NC NC
A1 🗖	4		41	A 18
A2 🗖	5		40	A 17
A3 🗖	6		39	A 16
A4 🗖	7		38	A 15
/CE 🗖	8		37	■/OE
I/O0 🗖	9	44-pin TSOP II	36	I/07
I/O1 🗖	10		35	I/O6
VCC 🗖	11		34	■ VSS
VSS 🗖	12		33	■ vcc
I/O2 🗖	13		32	I/O5
I/O3 🗖	14		31	I/O4
/WE 🗖	15		30	A 14
A5 🗖	16		29	A 13
A6 🗖	17		28	A 12
A7 🗖	18		27	A 11
A8 🗖	19		26	A 10
A9 🗖	20		25	NC NC
NC 🗖	21		24	NC NC
NC 🗖	22		23	■ NC



CY7C1049GN

Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage temperature	65 °C to +150 °C
Ambient temperature with power applied	55 °C to +125 °C
Supply voltage on V_{CC} relative to GND $^{[3]}$ 0	.5 to V _{CC} + 0.5 V
DC voltage applied to outputs in HI-Z State ^[3] –0.5	V to V _{CC} + 0.5 V

DC input voltage ^[3]	–0.5 V to V _{CC} + 0.5 V
Current into outputs (in LOW state) .	20 mA
Static discharge voltage (MIL-STD-883, Method 3015)	>2001 V
Latch-up current	> 140 mA

Operating Range

Grade	Ambient Temperature	V _{cc}
Industrial	–40 °C to +85 °C	1.65 V to 2.2 V, 2.2 V to 3.6 V, 4.5 V to 5.5 V

DC Electrical Characteristics

Over the operating range of -40 °C to 85 °C

Deveneter	Deser	ulunti o un	Toot Conditions	1	0 ns/15 n	S	11
Parameter	Desci	ription	Test Conditions	Min	Typ ^[4]	Max	Unit
V _{OH}	Output HIGH	1.65 V to 2.2 V	V _{CC} = Min, I _{OH} = -0.1 mA	1.4	_	_	V
	voltage	2.2 V to 2.7 V	V _{CC} = Min, I _{OH} = -1.0 mA	2	_	-	
		2.7 V to 3.0 V	V _{CC} = Min, I _{OH} = -4.0 mA	2.2	_	_	
		3.0 V to 3.6 V	V _{CC} = Min, I _{OH} = -4.0 mA	2.4	_	_	
		4.5 V to 5.5 V	V _{CC} = Min, I _{OH} = -4.0 mA	2.4	_	-	
		4.5 V to 5.5 V	V _{CC} = Min, I _{OH} = -0.1mA	$V_{CC} - 0.5^{[5]}$	_	_	
V _{OL}	Output LOW	1.65 V to 2.2 V	V _{CC} = Min, I _{OL} = 0.1 mA	-	_	0.2	V
	voltage	2.2 V to 2.7 V	V _{CC} = Min, I _{OL} = 2 mA	-	_	0.4	
		2.7 V to 3.6 V	V _{CC} = Min, I _{OL} = 8 mA	-	_	0.4	
		4.5 V to 5.5 V	V _{CC} = Min, I _{OL} = 8 mA	-	_	0.4	
V _{IH}		1.65 V to 2.2 V	_	1.4	_	$V_{CC} + 0.2^{[3]}$	V
	Input HIGH	2.2 V to 2.7 V	_	2	_	$V_{CC} + 0.3^{[3]}$	
	voltage	2.7 V to 3.6 V	_	2	_	$V_{CC} + 0.3^{[3]}$	
		4.5 V to 5.5 V	_	2	_	$V_{CC} + 0.5^{[3]}$	
V _{IL}		1.65 V to 2.2 V	_	-0.2 ^[3]	_	0.4	V
	Input LOW	2.2 V to 2.7 V	_	-0.3 ^[3]	_	0.6	
	voltage	2.7 V to 3.6 V	_	-0.3 ^[3]	_	0.8	
		4.5 V to 5.5 V	_	-0.5 ^[3]	_	0.8	
I _{IX}	Input leakage cu	irrent	$GND \le V_{IN} \le V_{CC}$	-1	_	+1	μA
I _{OZ}	Output leakage	current	$GND \leq V_{OUT} \leq V_{CC}$, Output disabled	-1	_	+1	μA
I _{CC}	Operating supply	y current	Max V_{CC} , $I_{OUT} = 0$ mA, $f = 100$ MHz CMOS levels	-	38	45	mA
			CMOS levels f = 66.7 MHz	<u> </u>	-	40	
I _{SB1}	Automatic CE po current – TTL in	ower-down puts	Max V _{CC} , <u>CE</u> ≥ V _{IH} , V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX}	-	_	15	mA
I _{SB2}	Automatic CE po current – CMOS		$\begin{array}{l} \text{Max V}_{\text{CC}}, \overline{\text{CE}} \geq \text{V}_{\text{CC}} - 0.2 \text{ V}, \\ \text{V}_{\text{IN}} \geq \text{V}_{\text{CC}} - 0.2 \text{ V} \text{ or } \text{V}_{\text{IN}} \leq 0.2 \text{ V}, \text{ f} = 0.2 \text{ V}. \end{array}$	_	6	8	mA

Notes

3. $V_{IL(min)} = -2.0 \text{ V}$ and $V_{IH(max)} = V_{CC} + 2 \text{ V}$ for pulse durations of less than 20 ns.

4. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = 1.8 V (for V_{CC} range of 1.65 V – 2.2 V), V_{CC} = 3 V (for V_{CC} range of 2.2V – 3.6 V), and V_{CC} = 5 V (for V_{CC} range of 4.5 V – 5.5 V), T_A = 25 °C.

5. This parameter is guaranteed by design and not tested.



Capacitance

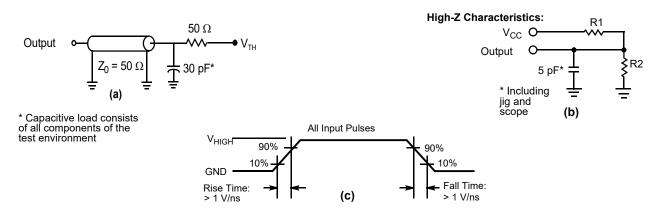
Parameter ^[6]	Description	Test Conditions	36-pin SOJ	44-pin TSOP II	Unit
C _{IN}	Input capacitance	$T_{A} = 25 \text{ °C}, f = 1 \text{ MHz},$	10	10	pF
C _{OUT}	I/O capacitance	$V_{CC} = V_{CC(typ)}$	10	10	pF

Thermal Resistance

Parameter [6]	Description	Test Conditions	36-pin SOJ	44-pin TSOP II	Unit
- JA		Still air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	59.52	68.85	°C/W
- 30	Thermal resistance (junction to case)		31.48	15.97	°C/W

AC Test Loads and Waveforms

Figure 3. AC Test Loads and Waveforms [7]



Parameters	1.8 V	3.0 V	5.0 V	Unit
R1	1667	317	317	Ω
R2	1538	351	351	Ω
V _{TH}	0.9	1.5	1.5	V
V _{HIGH}	1.8	3	3	V

Notes

- Tested initially and after any design or process changes that may affect these parameters.
 Full-device AC operation assumes a 100-μs ramp time from 0 to V_{CC(min)} and a 100-μs wait time after V_{CC} stabilization.



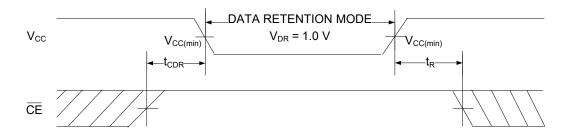
Data Retention Characteristics

Over the operating range of -40 °C to 85 °C

Parameter	Description	Conditions	Min	Max	Unit
V _{DR}	V _{CC} for data retention		1	-	V
I _{CCDR}	Data retention current	$V_{CC} = 1.2 \text{ V}, \overline{CE} \ge V_{CC} - 0.2 \text{ V}^{[8]}, V_{IN} \ge V_{CC} - 0.2 \text{ V}, \text{ or } V_{IN} \le 0.2 \text{ V}$	-	8	mA
t _{CDR} ^[9]	Chip deselect to data retention time		0	_	ns
t _R ^[8, 9]	Operation recovery time	V _{CC} ≥ 2.2 V	10	-	ns
		V _{CC} < 2.2 V	15	—	ns

Data Retention Waveform

Figure 4. Data Retention Waveform ^[8]



Notes

8. Full-device operation requires linear V_{CC} ramp from V_{DR} to V_{CC(min)} \geq 100 µs or stable at V_{CC (min)} \geq 100 µs.

9. These parameters are guaranteed by design.



AC Switching Characteristics

Over the operating range of -40 °C to 85 °C

Parameter ^[10]	Description	10	10 ns		15 ns	
Parameter [10]	Description	Min	Max	Min	Мах	Unit
Read Cycle			•	•		-
t _{RC}	Read cycle time	10	_	15	-	ns
t _{AA}	Address to data	_	10	-	15	ns
t _{OHA}	Data hold from address change	3	_	3	-	ns
t _{ACE}	CE LOW to data	-	10	-	15	ns
t _{DOE}	OE LOW to data	-	4.5	-	8	ns
t _{LZOE}	OE LOW to low impedance ^[11]	0	_	0	-	ns
t _{HZOE}	OE HIGH to High-Z ^[11]	-	5	-	8	ns
t _{LZCE}	CE LOW to low impedance ^[11]	3	_	3	-	ns
t _{HZCE}	CE HIGH to High-Z ^[11]	-	5	-	8	ns
t _{PU}	CE LOW to power-up ^[12, 13]	0	_	0	-	ns
t _{PD}	CE HIGH to power-down ^[12, 13]	-	10	-	15	ns
Write Cycle [13	3, 14]					
t _{WC}	Write cycle time	10	_	15	-	ns
t _{SCE}	CE LOW to write end	7	-	12	-	ns
t _{AW}	Address setup to write end	7	_	12	-	ns
t _{HA}	Address hold from write end	0	-	0	-	ns
t _{SA}	Address setup to write start	0	_	0	-	ns
t _{PWE}	WE pulse width	7	_	12	-	ns
t _{SD}	Data setup to write end	5	_	8	-	ns
t _{HD}	Data hold from write end	0	-	0	-	ns
t _{LZWE}	WE HIGH to low impedance ^[11]	3	-	3	-	ns
t _{HZWE}	WE LOW to High-Z ^[11]	-	5	-	8	ns

Notes

- 10. Test conditions assume a signal transition time (rise/fall) of 3 ns or less, timing reference levels of 1.5 V (for $V_{CC} \ge 3$ V) and $V_{CC}/2$ (for $V_{CC} < 3$ V), and input pulse levels of 0 to 3 V (for V_{CC} ≥ 3 V) and 0 to V_{CC} (for V_{CC} < 3 V). Test conditions for the read cycle use output loading, as shown in part (a) of Figure 3 on page 6, unless specified otherwise.
- 11. t_{HZOE}, t_{HZCE}, t_{HZCE}, t_{LZOE}, t_{LZOE}, t_{LZOE}, and t_{LZWE} are specified with a load capacitance of 5 pF, as shown in part (b) of Figure 3 on page 6. Transition is measured ±200 mV from steady state voltage.

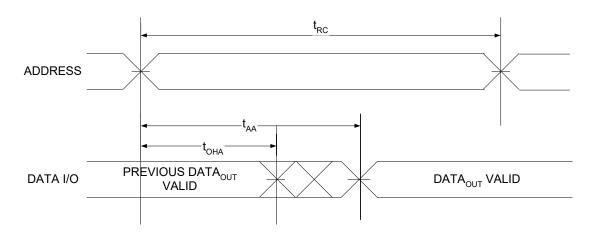
12. These parameters are guaranteed by design and are not tested.

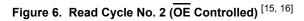
13. The internal write time of the memory is defined by the overlap of $\overline{WE} = V_{|L}$, $\overline{CE} = V_{|L}$. These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write. 14. The minimum write cycle pulse width in Write Cycle No. 2 (WE Controlled, \overline{OE} LOW) should be equal to sum of t_{DS} and t_{HZWE}.

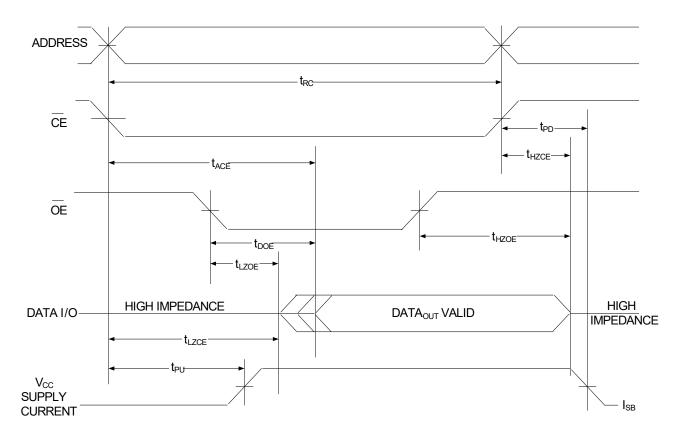


Switching Waveforms

Figure 5. Read Cycle No. 1 (Address Transition Controlled) ^[15, 16]







 $\begin{array}{l} \textbf{Notes} \\ \textbf{15. WE is HIGH for the read cycle.} \\ \textbf{16. Address valid prior to or coincident with \overline{CE} LOW transition.} \end{array}$



Switching Waveforms (continued)

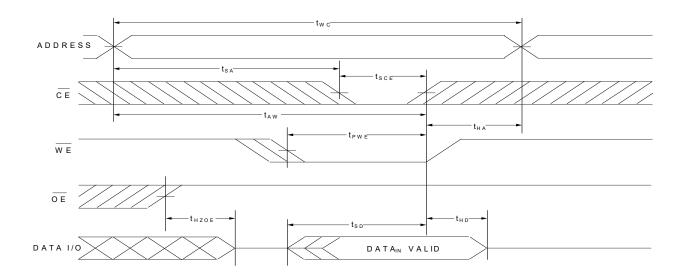
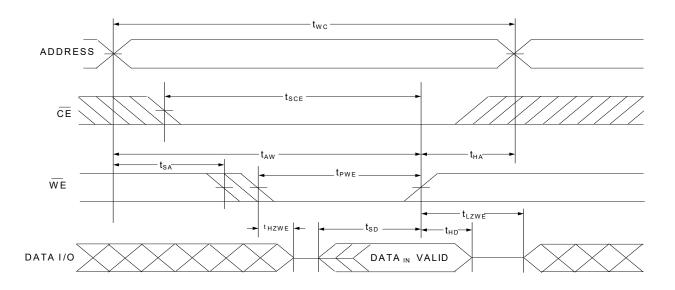


Figure 7. Write Cycle No. 1 (CE Controlled) ^[17, 18]

Figure 8. Write Cycle No. 2 (WE Controlled, OE LOW) [17, 18, 19]



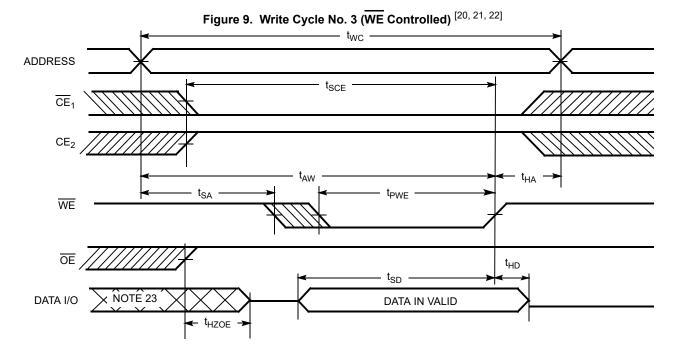
Notes

19. The minimum write cycle pulse width should be equal to sum of t_{SD} and t_{HZWE}.

^{17.} The internal write time of the memory is defined by the overlap of $\overline{WE} = V_{|L}$, $\overline{CE} = V_{|L}$. These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write. 18. Data I/O is in HI-Z state if $\overline{CE} = V_{|H}$, or $\overline{OE} = V_{|H}$.



Switching Waveforms (continued)



Notes

20. The internal write time of the memory is defined by the overlap of $\overline{WE} = V_{IL}$, $\overline{CE} = V_{IL}$. These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write. 21. Data I/O is in HI-Z state if $\overline{CE} = V_{IH}$, or $\overline{OE} = V_{IH}$.

23. During this period the I/Os are in output state. Do not apply input signals.

^{22.} Data I/O is high impedance if $\overline{\text{OE}}$ = V_{IH}.



Truth Table

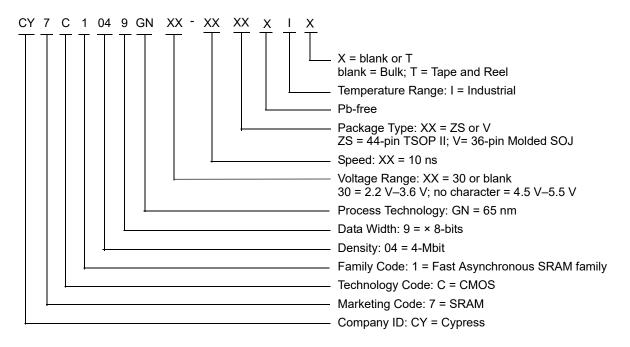
CE	OE	WE	I/O ₀ -I/O ₇	Mode	Power
Н	X ^[24]	X ^[24]	HI-Z	Power down	Standby (I _{SB})
L	L	Н	Data out	Read all bits	Active (I _{CC})
L	Х	L	Data in	Write all bits	Active (I _{CC})
L	Н	Н	HI-Z	Selected, outputs disabled	Active (I _{CC})



Ordering Information

Speed (ns)	Voltage Range	Ordering Code	Package Diagram	Package Type (all Pb-free)	Operating Range
10	2.2 V–3.6 V	CY7C1049GN30-10ZSXI	51-85087	44-pin TSOP II	Industrial
		CY7C1049GN30-10ZSXIT	51-85087	44-pin TSOP II, Tape and Reel	
		CY7C1049GN30-10VXI	51-85090	36-pin Molded SOJ	
		CY7C1049GN30-10VXIT	51-85090	36-pin Molded SOJ, Tape and Reel	
	4.5 V–5.5 V	CY7C1049GN-10VXI	51-85090	36-pin Molded SOJ	
		CY7C1049GN-10VXIT	51-85090	36-pin Molded SOJ, Tape and Reel	

Ordering Code Definitions





Package Diagrams

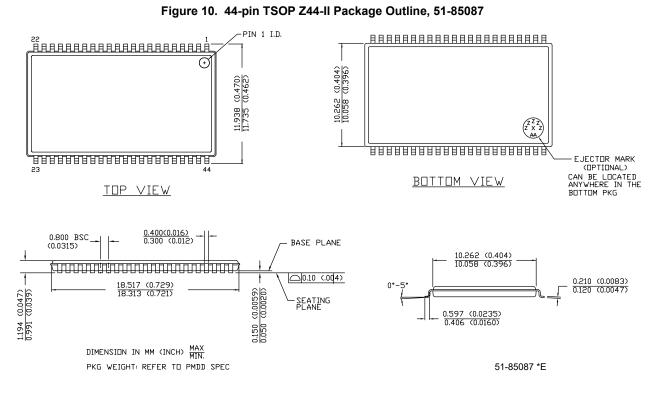
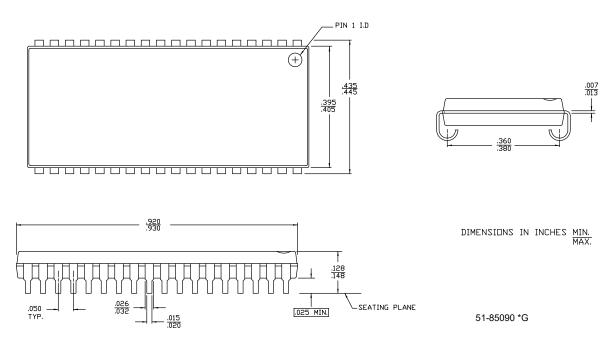


Figure 11. 36-pin SOJ V36.4 (Molded) Package Outline, 51-85090





Acronyms

Acronym	Description	
BHE	byte high enable	
BLE	byte low enable	
CE	chip enable	
CMOS	complementary metal oxide semiconductor	
I/O	input/output	
OE	output enable	
SRAM	static random access memory	
TSOP	thin small outline package	
TTL	transistor-transistor logic	
VFBGA	very fine-pitch ball grid array	
WE	write enable	

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	Degrees Celsius
MHz	megahertz
μA	microamperes
μs	microseconds
mA	milliamperes
mm	millimeter
ns	nanoseconds
Ω	ohms
%	percent
pF	picofarads
V	volts
W	watts





Document History Page

Document Document	Document Title: CY7C1049GN, 4-Mbit (512K words × 8-bit) Static RAM Document Number: 002-10613				
Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change	
**	5074703	NILE	01/06/2016	New data sheet.	
*A	5082587	NILE	01/12/2016	Updated Logic Block Diagram – CY7C1049GN. Updated Ordering Information: Updated part numbers.	
*В	5437570	NILE	09/15/2016	Updated DC Electrical Characteristics: Removed details of V _{OH} parameter corresponding to "2.7 V to 3.6 V" and Test Condition "V _{CC} = Min, I _{OH} = -4.0 mA". Added details of V _{OH} parameter corresponding to "2.7 V to 3.0 V" and Test Condition "V _{CC} = Min, I _{OH} = -4.0 mA". Added details of V _{OH} parameter corresponding to "3.0 V to 3.6 V" and Test Condition "V _{CC} = Min, I _{OH} = -4.0 mA". Added details of V _{OH} parameter corresponding to "3.0 V to 3.6 V" and Test Condition "V _{CC} = Min, I _{OH} = -4.0 mA". Changed minimum value of V _{IH} parameter corresponding to "4.5 V to 5.5 V" from 2.2 V to 2 V. Updated Note 3 (Replaced "2 ns" with "20 ns"). Updated Ordering Information: Updated part numbers. Updated to new template.	
*C	5966829	NILE	11/14/2017	Updated Switching Waveforms: Updated Figure 6. Updated Figure 7. Updated Figure 8. Updated Figure 9. Updated to new template. Completing Sunset Review.	



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